ABSTRACT

A tunnel junction device capable of controlling its spin retention is provided. The tunnel junction device includes a $\text{La}_{0.6}\text{Sr}_{0.4}\text{MnO}_{3-\delta}$ electrode (12), a $\text{La}_{0.6}\text{Sr}_{0.4}\text{Mn}_{1-\gamma}\text{Ru}_{\gamma}\text{O}_{3-\delta}$ electrode (14), both as ferromagnetic (including ferrimagnetic) metal materials, and a $\text{LaAlO}_{3-\delta}$ (electrically insulating layer) (13) arranged between the two electrodes (12) and (14).